8-input NAND gate Rev. 1 — 30 January 2013

1. **General description**

The 74HC30-Q100; 74HCT30-Q100 is an 8-input NAND gate. Inputs include clamp diodes. This enables the use of current limiting resistors to interface inputs to voltages in excess of V_{CC} .

This product has been qualified to the Automotive Electronics Council (AEC) standard Q100 (Grade 1) and is suitable for use in automotive applications.

2. Features and benefits

- Automotive product qualification in accordance with AEC-Q100 (Grade 1)
 - Specified from –40 °C to +85 °C and from –40 °C to +125 °C
- Complies with JEDEC standard JESD7A
- Input levels:
 - For 74HC30-Q100: CMOS level
 - For 74HCT30-Q100: TTL level
- ESD protection:
 - MIL-STD-883, method 3015 exceeds 2000 V
 - HBM JESD22-A114F exceeds 2000 V
 - MM JESD22-A115-A exceeds 200 V (C = 200 pF, R = 0 Ω)
- Multiple package options

Ordering information 3.

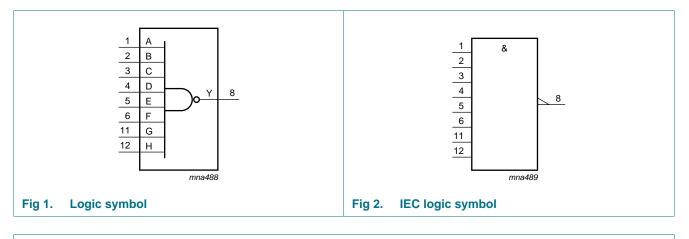
Table 1. **Ordering information**

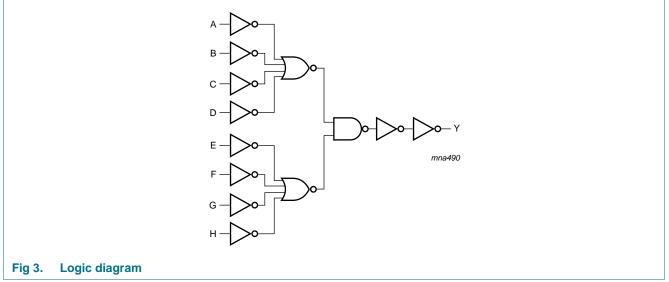
Type number	Package								
	Temperature range	Name	Description	Version					
74HC30D-Q100	–40 °C to +125 °C	SO14	plastic small outline package; 14 leads;	SOT108-1					
74HCT30D-Q100			body width 3.9 mm						
74HC30PW-Q100	–40 °C to +125 °C	TSSOP14	plastic thin shrink small outline package; 14 leads;	SOT402-1					
74HCT30PW-Q100			body width 4.4 mm						



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4. Functional diagram

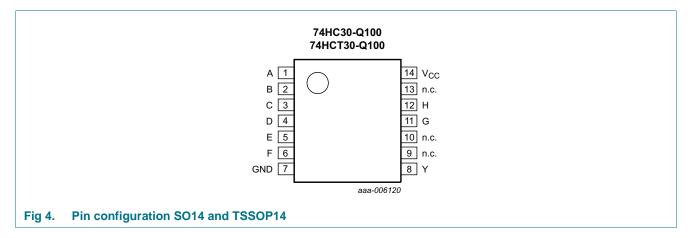




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5. Pinning information

5.1 Pinning



5.2 Pin description

Table 2.	Pin description	
Symbol	Pin	Description
A	1	data input
В	2	data input
С	3	data input
D	4	data input
E	5	data input
F	6	data input
GND	7	ground (0 V)
Y	8	data output
n.c.	9	not connected
n.c.	10	not connected
G	11	data input
Н	12	data input
n.c.	13	not connected
V _{CC}	14	supply voltage

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6. Functional description

Table 3.	Function	table ^[1]						
Input								Output
Α	В	С	D	E	F	G	Н	Y
L	Х	Х	Х	Х	Х	Х	Х	Н
Х	L	Х	Х	Х	Х	Х	Х	Н
Х	Х	L	Х	Х	Х	Х	Х	Н
Х	Х	Х	L	Х	Х	Х	Х	Н
Х	Х	Х	Х	L	Х	Х	Х	Н
Х	Х	Х	Х	Х	L	Х	Х	Н
Х	Х	Х	Х	Х	Х	L	Х	Н
Х	Х	Х	Х	Х	Х	Х	L	Н
Н	Н	Н	Н	Н	Н	Н	Н	L

[1] H = HIGH voltage level; L = LOW voltage level; X = don't care.

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

					-
Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		-0.5	+7	V
I _{IK}	input clamping current	$V_{\rm I}$ < –0.5 V or $V_{\rm I}$ > $V_{\rm CC}$ + 0.5 V	<u>[1]</u> _	±20	mA
Ι _{ΟΚ}	output clamping current	$V_{\rm O}$ < –0.5 V or $V_{\rm O}$ > $V_{\rm CC}$ + 0.5 V	<u>[1]</u> _	±20	mA
I _O	output current	$-0.5 \text{ V} < \text{V}_{\text{O}} < \text{V}_{\text{CC}} + 0.5 \text{ V}$	-	±25	mA
I _{CC}	supply current		-	50	mA
I _{GND}	ground current		-50	-	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation				
	SO14 and TSSOP14 packages		<u>[2]</u> -	500	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] For SO14 package: P_{tot} derates linearly with 8 mW/K above 70 $^\circ\text{C}.$

For TSSOP14 packages: P_{tot} derates linearly with 5.5 mW/K above 60 °C.

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8. Recommended operating conditions

Table 5. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V)

Symbol	ol Parameter Conditions		74HC30-Q100			74HCT30-Q100			Unit
			Min	Тур	Max	Min	Тур	Max	
V _{CC}	supply voltage		2.0	5.0	6.0	4.5	5.0	5.5	V
VI	input voltage		0	-	V _{CC}	0	-	V_{CC}	V
Vo	output voltage		0	-	V _{CC}	0	-	V_{CC}	V
T _{amb}	ambient temperature		-40	-	+125	-40	-	+125	°C
$\Delta t / \Delta V$	input transition rise and fall rate	$V_{CC} = 2.0 V$	-	-	625	-	-	-	ns/V
		$V_{CC} = 4.5 V$	-	1.67	139	-	1.67	139	ns/V
		$V_{CC} = 6.0 V$	-	-	83	-	-	-	ns/V

9. Static characteristics

Table 6. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		25 °C		–40 °C t	o +85 °C	–40 °C to	o +125 ℃	Unit
			Min	Тур	Max	Min	Max	Min	Max	
74HC30	-Q100								1	
V _{IH}	HIGH-level	$V_{CC} = 2.0 V$	1.5	1.2	-	1.5	-	1.5	-	V
	input voltage	$V_{CC} = 4.5 V$	3.15	2.4	-	3.15	-	3.15	-	V
		$V_{CC} = 6.0 V$	4.2	3.2	-	4.2	-	4.2	-	V
V _{IL}	LOW-level	$V_{CC} = 2.0 V$	-	0.8	0.5	-	0.5	-	0.5	V
	input voltage	$V_{CC} = 4.5 V$	-	2.1	1.35	-	1.35	-	1.35	V
		$V_{CC} = 6.0 V$	-	2.8	1.8	-	1.8	-	1.8	V
V _{OH} HIGH-level		$V_{I} = V_{IH} \text{ or } V_{IL}$								
	output voltage	$I_O = -20 \ \mu\text{A}; \ V_{CC} = 2.0 \ \text{V}$	1.9	2.0	-	1.9	-	1.9	-	V
		I_{O} = -20 μ A; V_{CC} = 4.5 V	4.4	4.5	-	4.4	-	4.4	-	V
		I_{O} = –20 $\mu A; V_{CC}$ = 6.0 V	5.9	6.0	-	5.9	-	5.9	-	V
		I_{O} = -4.0 mA; V_{CC} = 4.5 V	3.98	4.32	-	3.84	-	3.7	-	V
		I_{O} = -5.2 mA; V_{CC} = 6.0 V	5.48	5.81	-	5.34	-	5.2	-	V
V _{OL}	LOW-level	$V_{I} = V_{IH} \text{ or } V_{IL}$								
	output voltage	I_{O} = 20 μ A; V_{CC} = 2.0 V	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 20 \ \mu\text{A}; \ V_{CC} = 4.5 \ \text{V}$	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 20 \ \mu\text{A}; \ V_{CC} = 6.0 \ V$	-	0	0.1	-	0.1	-	0.1	V
		I_{O} = 4.0 mA; V_{CC} = 4.5 V	-	0.15	0.26	-	0.33	-	0.4	V
		I_{O} = 5.2 mA; V_{CC} = 6.0 V	-	0.16	0.26	-	0.33	-	0.4	V
1	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 6.0 V$	-	-	±0.1	-	±1	-	±1	μΑ
СС	supply current		-	-	2.0	-	20	-	40	μΑ

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Symbol	Parameter	Conditions		25 °C		–40 °C t	o +85 °C	–40 °C t	o +125 °C	Unit
			Min	Тур	Max	Min	Max	Min	Max	
CI	input capacitance		-	3.5	-	-	-	-	-	pF
74HCT3	0-Q100									
V _{IH}	HIGH-level input voltage	V_{CC} = 4.5 V to 5.5 V	2.0	1.6	-	2.0	-	2.0	-	V
V _{IL}	LOW-level input voltage	V_{CC} = 4.5 V to 5.5 V	-	1.2	0.8	-	0.8	-	0.8	V
V _{OH}	HIGH-level	$V_{I} = V_{IH} \text{ or } V_{IL}; V_{CC} = 4.5 \text{ V}$								
	output voltage	I _O = -20 μA	4.4	4.5	-	4.4	-	4.4	-	V
		$I_{O} = -4.0 \text{ mA}$	3.98	4.32	-	3.84	-	3.7	-	V
V _{OL} LOW-leve	LOW-level	$V_{I} = V_{IH} \text{ or } V_{IL}; V_{CC} = 4.5 \text{ V}$								
	output voltage	I _O = 20 μA	-	0	0.1	-	0.1	-	0.1	V
		I _O = 4.0 mA	-	0.15	0.26	-	0.33	-	0.4	V
I	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 5.5 V$	-	-	±0.1	-	±1	-	±1	μΑ
I _{CC}	supply current	$\label{eq:VI} \begin{array}{l} V_{I} = V_{CC} \text{ or } GND; \ I_{O} = 0 \ A; \\ V_{CC} = 5.5 \ V \end{array}$	-	-	2.0	-	20	-	40	μΑ
ΔI _{CC}	additional supply current	per input pin; $V_I = V_{CC} - 2.4 \text{ V}; I_O = 0 \text{ A};$ other inputs at V_{CC} or GND; $V_{CC} = 4.5 \text{ V}$ to 5.5 V	-	60	216	-	275	-	294	μA
CI	input capacitance		-	3.5	-	-	-	-	-	pF

Table 6. Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

10. Dynamic characteristics

Table 7. Dynamic characteristics

GND = 0 V; $C_L = 50$ pF; for test circuit see <u>Figure 6</u>.

Symbol	Parameter	Conditions			25 °C		–40 °C to +125 °C		Unit
				Min	Тур	Max	Max (85 °C)	Max (125 °C)	_
74HC30-	Q100								
t _{pd}	propagation delay	A, B, C, D, E, F, G, H to Y; see <u>Figure 5</u>	<u>[1]</u>						
		$V_{CC} = 2.0 V$		-	41	130	165	195	ns
		$V_{CC} = 4.5 V$		-	15	26	33	39	ns
		$V_{CC} = 5.0 \text{ V}; \text{ C}_{L} = 15 \text{ pF}$		-	12	-	-	-	ns
		$V_{CC} = 6.0 V$		-	12	22	28	33	ns
tt	transition time	see <u>Figure 5</u>	[2]						
		$V_{CC} = 2.0 V$		-	19	75	95	110	ns
		$V_{CC} = 4.5 V$		-	7	15	19	22	ns
		$V_{CC} = 6.0 V$		-	6	13	16	19	ns

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Symbol	Parameter	Conditions			25 °C		–40 °C to	o +125 °C	Unit
				Min	Тур	Мах	Max (85 °C)	Max (125 °C)	
C _{PD}	power dissipation capacitance	per package; $V_I = GND$ to V_{CC}	<u>[3]</u>	-	15	-	-	-	pF
74HCT30)-Q100								
t _{pd} propagation dela	propagation delay	A, B, C, D, E, F, G, H to Y; see <u>Figure 5</u>	<u>[1]</u>						
		$V_{CC} = 4.5 V$		-	16	28	35	42	ns
		$V_{CC} = 5.0 \text{ V}; \text{ C}_{L} = 15 \text{ pF}$		-	12	-	-	-	ns
t _t	transition time	$V_{CC} = 4.5 \text{ V}; \text{ see } \frac{\text{Figure 5}}{1000}$	[2]	-	7	15	19	22	ns
C _{PD}	power dissipation capacitance	per package; V _I = GND to V _{CC} – 1.5 V	[3]	-	15	-	-	-	pF

Table 7. Dynamic characteristics ...continued GND = 0 V: $C_1 = 50$ pE: for test circuit see Figure 6

[1] t_{pd} is the same as t_{PHL} and t_{PLH} .

[2] t_t is the same as t_{THL} and t_{TLH} .

[3] C_{PD} is used to determine the dynamic power dissipation (P_D in μ W):

 $P_{D} = C_{PD} \times V_{CC}^{2} \times f_{i} \times N + \sum (C_{L} \times V_{CC}^{2} \times f_{o}) \text{ where:}$

 f_i = input frequency in MHz;

 f_o = output frequency in MHz;

 C_L = output load capacitance in pF;

 V_{CC} = supply voltage in V;

N = number of inputs switching;

 $\sum (C_L \times V_{CC}^2 \times f_o)$ = sum of outputs.

11. Waveforms

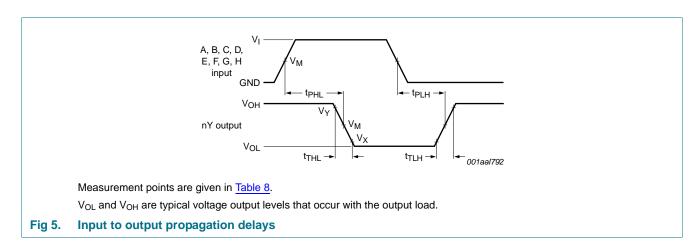


Table 8.Measurement points

Туре	Input	Output						
	V _M	V _M	V _X	V _Y				
74HC30-Q100	0.5V _{CC}	0.5V _{CC}	0.1V _{CC}	0.9V _{CC}				
74HCT30-Q100	1.3 V	1.3 V	0.1V _{CC}	0.9V _{CC}				

74HC_HCT30_Q100	
Product data	shoot

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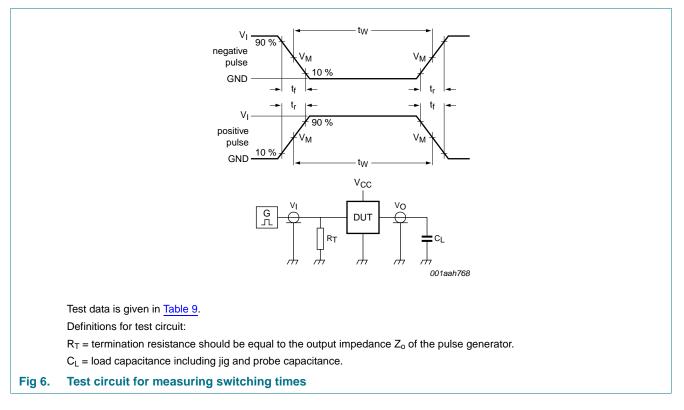


Table 9. Test data

Туре	Input	Input L		Test
	VI	t _r , t _f	CL	
74HC30-Q100	V _{CC}	6.0 ns	15 pF, 50 pF	t _{PLH} , t _{PHL}
74HCT30-Q100	3.0 V	6.0 ns	15 pF, 50 pF	t _{PLH} , t _{PHL}

8-input NAND gate

12. Package outline

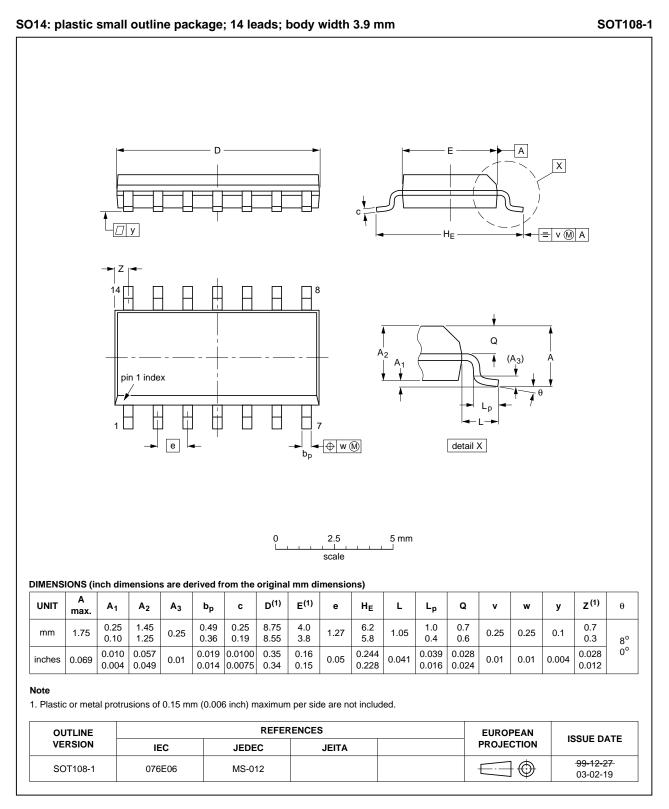


Fig 7. Package outline SOT108-1 (SO14)

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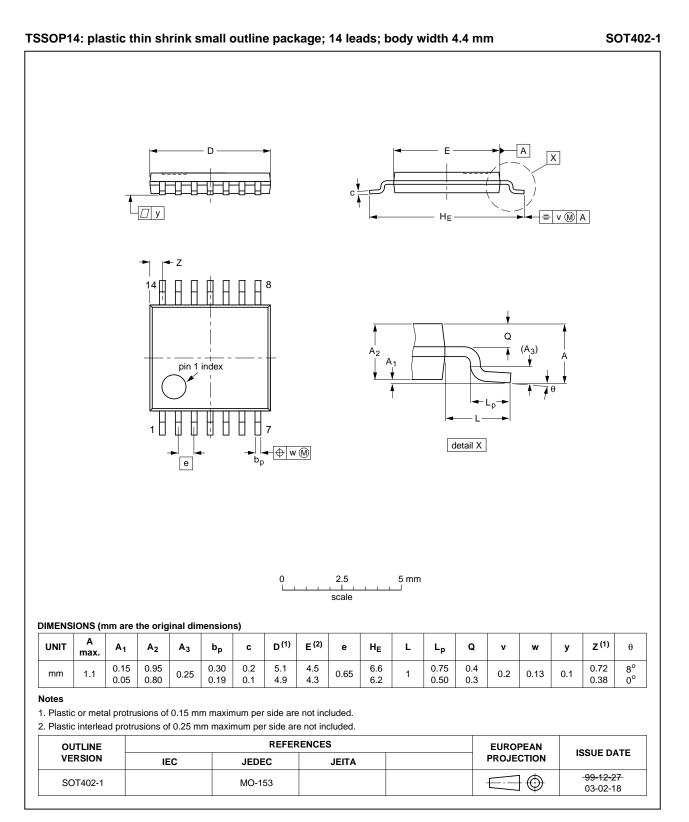


Fig 8. Package outline SOT402-1 (TSSOP14)

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13. Abbreviations

Table 10. Abbreviations		
Acronym	Description	
CMOS	Complementary Metal-Oxide Semiconductor	
DUT	Device Under Test	
ESD	ElectroStatic Discharge	
HBM	Human Body Model	
LSTTL	Low-power Schottky Transistor-Transistor Logic	
MM	Machine Model	
MIL	Military	
TTL	Transistor-Transistor Logic	

14. Revision history

Table 11. Revision hist	able 11. Revision history						
Document ID	Release date	Data sheet status	Change notice	Supersedes			
74HC_HCT30_Q100 v.1	20130130	Product data sheet	-	-			

74HC_HCT30_Q100

15. Legal information

15.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Date of release: 30 January 2013 Document identifier: 74HC_HCT30_Q100